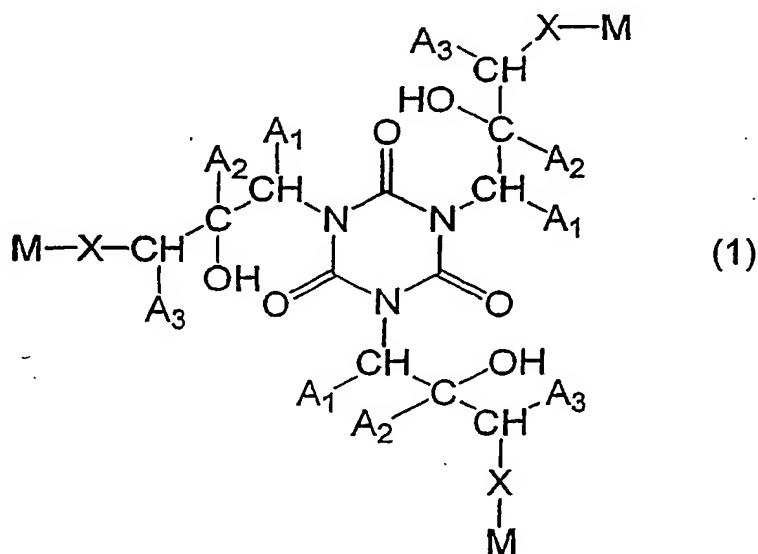


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A composition for forming anti-reflective coating characterized in that the composition comprises a triazine trione compound having hydroxyalkyl structure as substituent on nitrogen atom, a triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or a triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom.

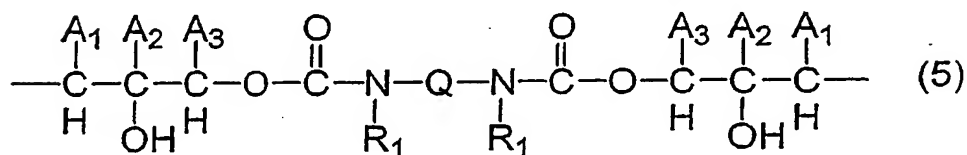
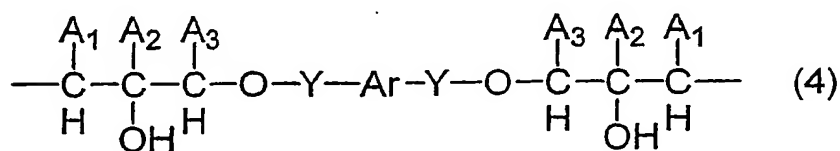
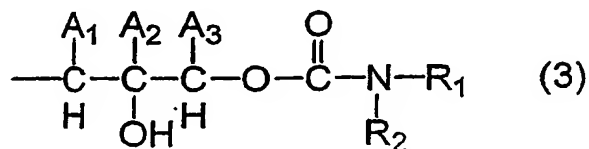
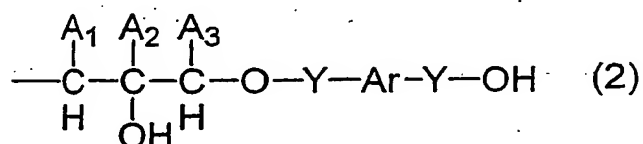
2. (Original) The composition for forming anti-reflective coating according to claim 1, wherein the triazine trione compound having hydroxyalkyl structure as substituent on nitrogen atom is a compound of formula (1):



wherein A₁, A₂ and A₃ are independently of one another hydrogen atom, methyl or ethyl, X is -OC(=O)-, -S-, -O- or -NR- wherein R is hydrogen atom or methyl, M is benzene ring, naphthalene ring or anthracene ring which may be substituted with C₁₋₆ alkyl, phenyl, naphthyl, halogen atom, C₁₋₆ alkoxy, cyano, C₁₋₆ alkoxy or C₁₋₆ alkylthio.

3. (Currently Amended) The composition for forming anti-reflective coating according to claim 1, wherein the triazine trione compound having hydroxyalkyl structure as

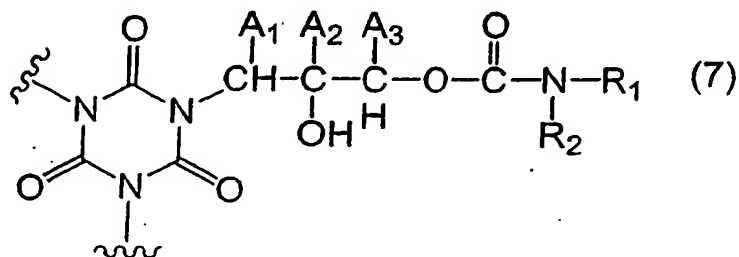
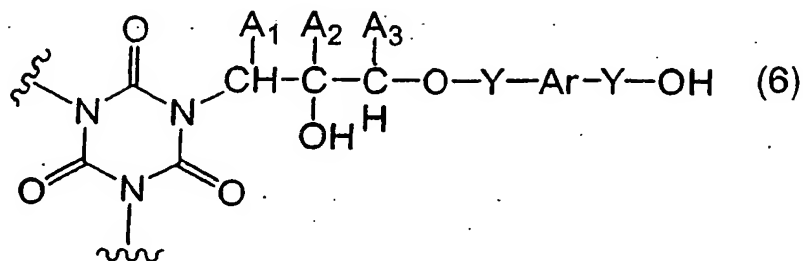
substituent on nitrogen atom, the triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or the triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom is a triazine trione compound having a substituent of formula (2) or (3) as substituent on nitrogen atom, or a triazine trione oligomer compound or triazine trione polymer compound having a structure in which at least two triazine trione rings are linked through a linking group of formula (4) or (5) on the nitrogen atoms:



wherein A_1 , A_2 and A_3 ~~have the same meaning as that in claim 2~~ are independently of one another hydrogen atom, methyl or ethyl, X is $-OC(=O)-$, $-S-$, $-O-$ or $-NR-$ wherein R is hydrogen atom or methyl, Y is a direct bond or $-C(=O)-$, Ar is benzene ring or naphthalene ring which may be substituted with C_{1-6} alkyl, phenyl, naphthyl, halogen atom, C_{1-6} alkoxy, carbonyl, nitro, carboxy, cyano, C_{1-6} alkoxy, hydroxy, thiol, C_{1-6} alkylthio or amino, Q is C_{1-6} alkyl, C_{5-8} cycloalkyl, Ar or $-CH_2-Ar-CH_2-$, R_1 is C_{1-6} alkyl, phenyl or benzyl, R_2 is hydrogen atom, C_{1-6} alkyl, phenyl or benzyl.

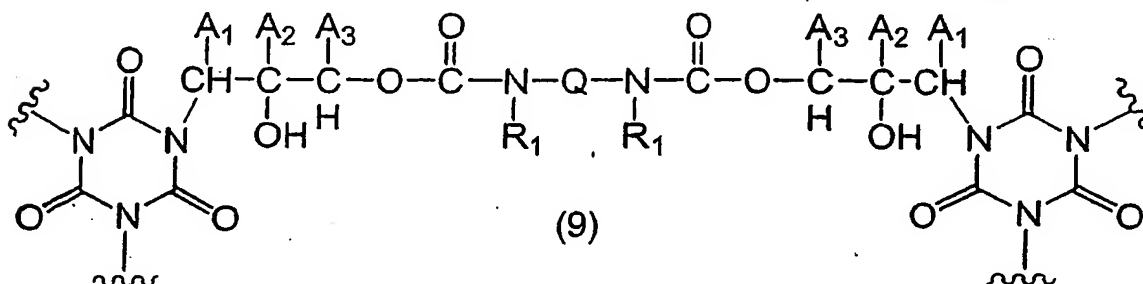
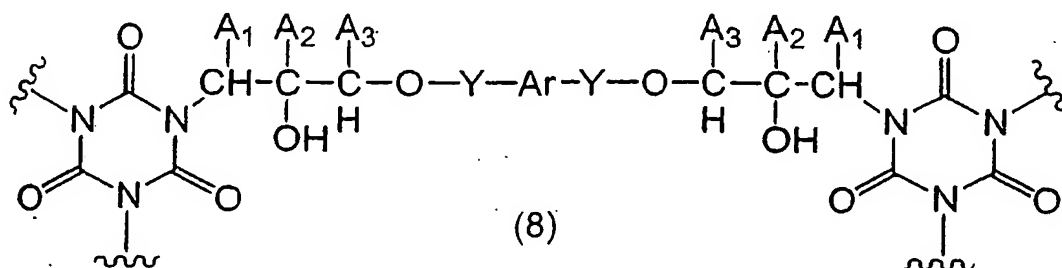
4. (Currently Amended) The composition for forming anti-reflective coating according to claim 3, wherein the triazine trione compound having a substituent of formula

(2) or (3) has a structure of formula (6) or (7):



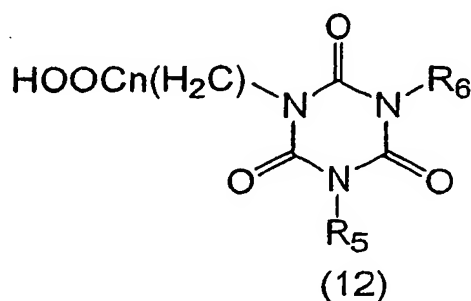
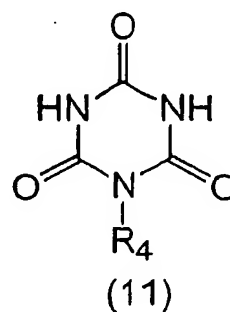
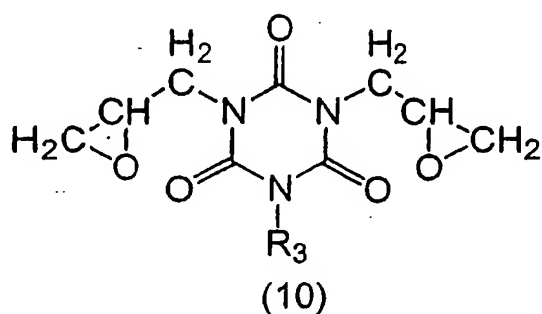
wherein A_1 , A_2 , A_3 , Y , Ar , R_1 and R_2 have the same meaning as that in claim 3.

5. (Currently Amended) The composition for forming anti-reflective coating according to claim 3, wherein the triazine trione oligomer compound or triazine trione polymer compound having a structure in which at least two triazine trione rings are linked through a linking group of formula (4) or (5) on the nitrogen atoms has a structure of formula (8) or (9):



wherein A_1 , A_2 , A_3 , Y , Ar , Q , R_1 and R_2 have the same meaning mentioned as that in claim 3.

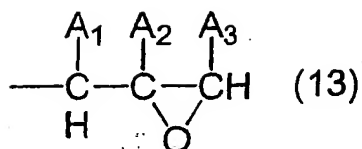
6. (Original) The composition for forming anti-reflective coating according to claim 1, wherein the triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom is a reaction product of a compound of formula (10) with a compound of formula (11) or (12):



wherein R_3 is C_{1-6} alkyl, C_{3-6} alkenyl, phenyl, benzyl or 2,3-epoxypropyl, R_4 and R_5 are C_{1-6} alkyl, C_{3-6} alkenyl, phenyl or benzyl, R_6 is C_{1-6} alkyl, phenyl, benzyl or $-(CH_2)_nCOOH$, and n is a number of 1, 2 or 3.

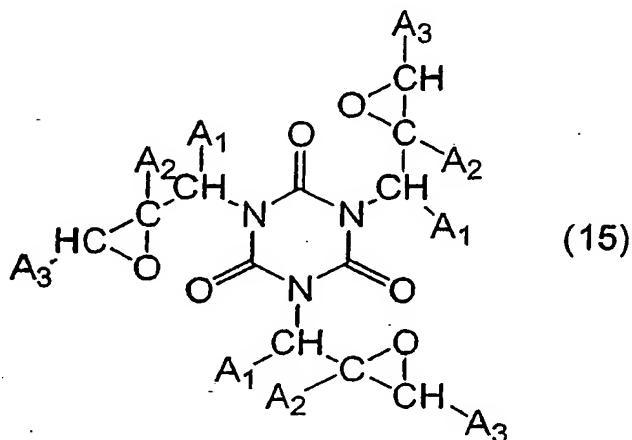
7. (Currently Amended) The composition for forming anti-reflective coating according to claim 3, wherein the triazine trione compound having a substituent of formula (2) as substituent on nitrogen atom, or the triazine trione oligomer compound or triazine trione polymer compound having a structure in which at least two triazine trione rings are linked through a linking group of formula (4) on the nitrogen atoms is produced from a triazine trione compound having at least two nitrogen atoms having a substituent of formula (13) on nitrogen atom and a phenyl compound or naphthalene compound of formula (14) having at least two substituents selected from carboxy and hydroxy which are identical or

different from each other



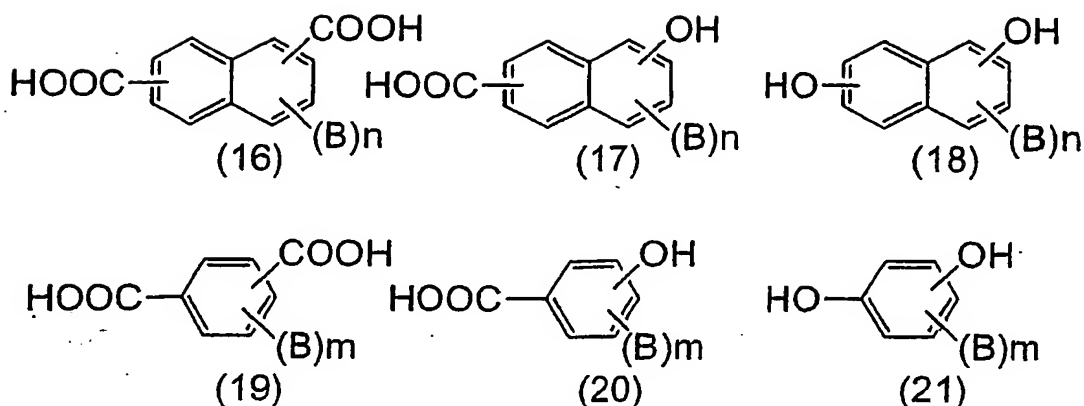
~~in formula (13), A₁, A₂ and A₃ have the same meaning as that in claim 3, and in formula (14), Y and Ar have the same meaning as that in claim 3.~~

8. (Currently Amended) The composition for forming anti-reflective coating according to claim 7, wherein triazine trione compound having at least two nitrogen atoms having a substituent of formula (13) on nitrogen atom is a triazine trione compound of formula (15)



~~wherein A₁, A₂ and A₃ have the same meaning as that in claim 3.~~

9. (Original) The composition for forming anti-reflective coating according to claim 7, wherein the phenyl compound or naphthalene compound of formula (14) is at least one compound selected from the group consisting of compounds of formulae (16) to (21)



wherein B is hydrogen atom, C₁₋₆ alkyl, phenyl, naphthyl, halogen atom, C₁₋₆ alkoxycarbonyl, nitro, carboxy, cyano, C₁₋₆ alkoxy, hydroxy, thiol, C₁₋₆ alkylthio or amino, n is a number of 1 to 6, m is a number of 1 to 4, and B may be identical with or different from each other in case where n or m is 2 or more.

10. (Currently Amended) The composition for forming anti-reflective coating according to ~~any one of claims 1 to 9~~claim 1, further containing a crosslinking agent having at least two crosslink-forming substituents.

11. (Currently Amended) The composition for forming anti-reflective coating according to ~~any one of claims 1 to 10~~claim 1, further containing an acid and/or an acid generator.

12. (Currently Amended) The composition for forming anti-reflective coating according to ~~any one of claims 1 to 11~~claim 1, further containing a resin having at least one crosslinking-forming substituent selected from hydroxy, carboxy, amino and thiol.

13. (Currently Amended) An anti-reflective coating produced by coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 12~~claim 1 on a semiconductor substrate, and baking it, wherein the anti-reflective coating has an attenuation coefficient k to a light at a wavelength of 248 nm ranging from 0.40 to 0.65.

14. (Currently Amended) An anti-reflective coating produced by coating the

composition for forming anti-reflective coating according to ~~any one of claims 1 to 12~~claim 1 on a semiconductor substrate, and baking it, wherein the anti-reflective coating has an attenuation coefficient k to a light at a wavelength of 157 nm ranging from 0.20 to 0.50.

15. (Currently Amended) An anti-reflective coating produced by coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 12~~claim 1 on a semiconductor substrate, and baking it, wherein the anti-reflective coating has an attenuation coefficient k to a light at a wavelength of 193 nm ranging from 0.20 to 0.60.

16. (Currently Amended) A method of forming an anti-reflective coating for use in a manufacture of a semiconductor device, comprising the steps of: coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 12~~claim 1 on a substrate, and baking it.

17. (Currently Amended) A method of forming an anti-reflective coating for use in a manufacture of a semiconductor device by use of a light of wavelength 248 nm, 193 nm or 157 nm, comprising the steps of: coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 12~~claim 1 on a substrate, and baking it.

18. (Currently Amended) A method of forming a photoresist pattern for use in a manufacture of a semiconductor device comprising the steps of:
coating the composition for forming anti-reflective coating according to ~~any one of claims 1 to 12~~claim 1 on a semiconductor substrate and baking it to form an anti-reflective coating,
forming a photoresist layer on the anti-reflective coating,
exposing the semiconductor substrate covered with the anti-reflective coating and the photoresist layer with a light, and
developing the exposed photoresist layer.

19. (Original) The method of forming a photoresist pattern according to claim 18, wherein the exposure is carried out with a light of wavelength 248 nm, 193 nm or 157 nm.